

## **ABSTRACT OF THE DISCLOSURE**

1           A semiconductor integrated circuit device, and method of manufacturing the same,  
2 includes an inductor with improved inductance and an improved quality factor (Q-factor) that  
3 can be miniaturized. In one example, an inductor (3) is provided on an insulating layer (2) of  
4 a multilayer interconnection layer (1). The inductor (3) is formed by a spiral arrangement of  
5 a wiring (3a). A lamination film (14) is provided in an internal region (13) of an inductor (3)  
6 on insulating layer (2), and can be formed by laminating a titanium-tungsten (TiW) layer (9),  
7 a copper (Cu) layer (10), a ferromagnetic substance layer (15) made of nickel (Ni), a Cu layer  
8 (11), and a TiW layer (12), in that order. A lower surface of ferromagnetic substance layer  
9 (15) can be lower than an upper surface of wiring layer (3a), and an upper surface of  
10 ferromagnetic substance layer (15) can be higher than a lower surface of wiring layer (3a).  
11 As a result, a lower portion of ferromagnetic substance layer (15) can be at the same layer  
12 (level) as wiring layer (3a). An upper surface of lamination film (14) can be made higher  
13 than a wiring layer (3a), and a lower surface of lamination film (14) can be made lower than  
14 a lower surface of a wiring layer (3a).